Fermilab Department of Science



Modeling Interactions of MeV-Scale DM with Crystal Targets: Plasmons, Phonons, and Lattice Defects

Noah Kurinsky Physics Seminar, INFN-Roma March 15, 2021

> + Dan Baxter, Gordan Krnjaic, Yonatan Kahn arXiv:2002.06937 Phys. Rev. D 102, 015017 (2020)

Featured in Scientific American



PHYSICS

Direct Proof of Dark Matter May Lurk at Low-Energy Frontiers

Mysterious effects in a new generation of dark matter detectors could herald a revolutionary discovery

أعرض هذا باللغة العربية By Daniel Garisto on June 9, 2020





Searching for Dark Matter in the Inelastic Regime

Daniel Baxter HEP Seminar University of California, Santa Barbara

September 28, 2020



Photo Credit: Getty Images



Overview

- Kinematics of Sub-GeV DM
- Current Constraints
 - ER Searches
 - NR Searches
 - Summary of Excesses
- Modeling Excesses
 - Yield comparison
 - Elimination of SM Processes
 - Brief plasmon description
- Possible DM Interpretations



What Drives Low-Mass Detector Reach?

- Dark matter mass determines two quantities: local dark matter number density and recoil energy distribution
 - Mass density set by astrophysical constraints
- For low mass, sensitivity is limited by your energy threshold; lighter
 particles will transfer less energy to your target, and heavier nuclei will further suppress this transfer
- For high mass, increasing mass decreases number density; heavier target provides larger cross-section and therefore more exposure





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- Low mass detectors can be small, as long as they have low energy thresholds!





Collision Kinematics

- Recoil energy for typical DM velocity depends on target mass and recoil type
- Electron and nuclear recoils have different kinematics; nuclear recoils are simple elastic collisions, electron recoils are largely inelastic and depend on electron orbital and kinematics within the bound electron-atom system
- In addition to momentum transfer for a fixed velocity, using a velocity and angular distribution yields an expected energy spectrum

$$\Delta E_{NR} \leq \frac{1}{2m_N} q_{max}^2 = \frac{m_N v^2}{2} \left(\frac{2m_\chi}{m_\chi + m_N}\right)^2$$
$$\Delta E_{ER} \leq \frac{1}{2} \mu_{N\chi} v^2 = \frac{m_N v^2}{2} \left(\frac{m_\chi}{m_\chi + m_N}\right)$$



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$$m_{\chi,ER} \ge \frac{2\sigma_E}{v^2}$$



Collision Kinematics



Revised DM Kinematics

- Free-particle regime (DM KE > keV):
 - DM interactions probe core electrons
 - DM will liberate nuclei with energies > 1keV),
 - Interaction can be treated pseudo-classically
- Bound-particle regime (DM KE < eV)
 - Electron interactions frozen out
 - Lattice defects can't be created
 - Only relevant processes are phonon creation in solid-state materials
- Collective Regime (DM KE > eV, < keV)
 - Corresponds to the MeV GeV mass regime
 - Energy depositions *comparable to inelastic energy scales*
 - Detailed band structure important for electron recoils
 - Liberation of free nucleon from the lattice *not guaranteed*; energy loss mechanisms important



Berggren, Hochberg, Kahn, NK, Lehman, Yu, ArXiv:2101.08263

Low Mass (< GeV) Dark Matter

- Dark matter in the keV-GeV mass range can produce the correct DM relic density if we introduce a new mediator between the DM and SM
- Consider a massive 'dark photon' mediator coupled to a heavy particle which does not interact with SM as the only particles in a new 'dark sector'
 - If the mediator is heavier, dark matter can freeze out for the right coupling strengths in the same way as WIMP DM
 - If the dark photon is the lighter particle, it can 'freeze in' as the 'heavy' DM decays into dark photons and SM particles
- Much of the simplest parameter space completely unconstrained in the freeze-in scenario due to the momentum suppression
- Lots of theory work done on these models in the last few years and multiple workshop reports



$$\langle \sigma_A v \rangle \propto \frac{g_D^4}{m_\chi^2} \qquad \langle \sigma_A v \rangle \propto \frac{g_D^2 g_{SM}^2 m_\chi^2}{m_{med}^4}$$

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3/15/2021

DM Search Strategies

Dark Sector Candidates, Anomalies, and Search Techniques





DM Search Strategies

Dark Sector Candidates, Anomalies, and Search Techniques



 New mass ranges considered in dark-sector DM interactions are also where understanding material inelasticity becomes most important!

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Detecting DM Recoils



Figure from Yonatan Kahn

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High Resolution CCDs: DAMIC, SENSEI, DANAE*

- Electron and nuclear recoils produce electron-hole pairs in Si, which are stored in pixels during the exposure
- Charges moved to set of charge amplifiers during readout
 - Single read noise limited by charge amplifier and electronics noise
 - Skipper CDDs capable of non-destructive read; can re-sample the same pixel and arbitrary number of times
- Arbitrarily low resolution (in ideal case) at the expense of readout time. Very large dynamic range, excellent position resolution and event tracking
- No differentiation between paired and unpaired charge carrriers; operation at ~100K ensures some thermally generated carriers

Tiffenberg et. al. 2017 (arXiv:1706.00028)



Athermal Phonon Sensors (SuperCDMS, EDELWEISS)

- In any recoil event, all energy eventually returns to the phonon system
 - Prompt phonons produced by interaction with nuclei
 - Indirect-gap phonons produced by charge carriers reaching band minima
 - Recombination phonons produced when charge carriers drop back below the band-gap
- Phonons are also produced when charges are drifted in an electric field; makes sense by energy conservation alone
- Total phonon energy is initial recoil energy plus Luke phonon energy, as shown at right

$$E_{phonon} = E_{recoil} + V * n_{eh}$$
$$= E_{recoil} \left[1 + V * \left(\frac{y(E_{recoil})}{\varepsilon_{eh}} \right) \right]$$

 Athermal phonons collected in superconducting aluminum fins and channeled into Tungsten TES, effectively decoupling crystal heat capacity from calorimeter (TES) heat capacity







Romani et. al. 2017 (<u>https://arxiv.org/abs/1710.09335</u>)

https://arxiv.org/abs/1206.2644 100 104 Best fit https://arxiv.org/abs/1804.00088 Allowed at 90% upper limit Counts / 0.1 electrons Exposure: 0.019 gram-days Raw spectrum 10³ 15 kg-days Entries 10² single electron 10 loubl electron triple Effic. crosses 5% electron 0. 10 2 3 5 Charge [e] https://arxiv.org/abs/1804.00088 Differential Event Rate (Hz/n_{eh}) 10^{1} Data Direct detection limits on sub-GeV dark matter 0.5 gram-days Laser 10^{0} MC qd 10⁸ Dark Photon $m_V = 9.4 \text{ eV}$ 10 $\varepsilon_{eff} = 5 \cdot 10^{-13}$ DM-electron cross-section 10 10⁴ 10 100 Sensitivity determined by background, ENO DarkSide-50 exposure, and resolution 0.01 F_{DM}=1 0.010 0.100 0.001 Pileup rejection important for IR-limited Dark Matter Mass [GeV] background http://resonaances.blogspot.com/2018/05/dark-matter-goes-sub-gev.html

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Comparison of ER Experiments (2018)



Comparison of ER Experiments (2019)

HVeV Run 2



- HVeV second run taken with 3 eV resolution detector over the course of 3 weeks:
 - 60V and 100V spectra show identical backgrounds; signal seen not voltage dependent
 - Different prototype, run in a different lab, in a different state
 - 0V data acquired with ~12 eV threshold, results still being analyzed
 - Rates in every charge bin consistent with Run 1...that is completely unexpected





Comparison of ER Experiments (2020)

Cerenkov Photon Backgrounds



- Reduction of SENSEI background correlated with lower background and rejection of photons near high-energy tracks
- Recent paper demonstrated that the R1/R2 backgrounds can be explained by Cherenkov photons from mount PCBs
 - Also explored transition radiation, which is next leading background at the gram-day level



HVeV Run 3 Status

- Science run currently underway with 3 detectors (including detectors used for Runs 1-2, and a third new design)
 - Using coincidence in time to reject bursts of Cherenkov photons
 - Building model of leakage pileup to project component of single charge leakage in second electron-hole pair bin
 - Still expect single-electron bin is instrumental
- Run started 12/23, officially ended 2/9
 - Accumulating ~1 g-days per calendar day
 - Estimate ~40 g-days of exposure by end of run
- Quick turn around expected on analysis, new results by June 2021
 - *Many* auxiliary science results to follow on 0V-HV correlations



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Semiconductors Summary

Readout Type	Target	Resolution	Exposure	Threshold	Excess Rate (Hz/kg)	Depth	Reference
Charge (E_e)	Ge	$1.6 \ e^-$	$80 \text{ g} \cdot \text{d}$	$0.5 \text{ eVee } (\sim 1e^{-})^{\text{a}}$	[20, 100]	$1.7 \mathrm{km}$	EDELWEISS [6]
	Si	${\sim}0.2~e^-$	$0.18 \mathrm{g} \cdot \mathrm{d}$	$1.2 \text{ eVee} (< 1 e^{-})$	[4e-2,4]	100 m	SENSEI [4]
	Si	$0.1 \ e^-$	$0.5 \text{ g} \cdot \text{d}$	$1.2 \text{ eVee} (< 1 e^{-})$	[10, 2000]	$\sim 1 \text{ m}$	CDMS HVeV [3]
	Si	$1.6~e^-$	$200 \text{ g} \cdot \text{d}$	$1.2 \text{ eVee} (\sim 1e^{-})$	$[1 \times 10^{-3}, 7]$	$2 \mathrm{km}$	DAMIC [7]

Intriguing coincidence of rates

Different Depths Different Shielding Different Exposures Different Composition Different Temperatures Different Pressures

Unlike nuclear recoil: these are integrated total rates! Semiconductors have tiny thresholds



All Sub-GeV DM Searches

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	CaWO ₄	$4.6 \mathrm{eV}$	$3600 \mathrm{g} \cdot \mathrm{d}$	$30 \mathrm{eV}$	$> 3 \times 10^{-3}$	4 km	CRESST-III [2]
	Al_2O_3	$3.8 \mathrm{eV}$	$0.046 \text{ g} \cdot \text{d}$	20 eV	> 30	$\sim 1 \text{ m}$	ν CLEUS [8]
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	Xe	$6.2 \text{ PE} (\sim 0.31 e^{-})$	$30 \text{ kg} \cdot \text{yr}$	$\sim 70 \text{ eVee} (\sim 80 \text{ PE})$	$> 2.2 \times 10^{-5}$	4 km	XENON100 [5]
	Xe	< 10 PE	$60 \text{ kg} \cdot \text{yr}$	$\sim 140 \text{ eVee} (\sim 90 \text{ PE})$	$> 1.7 \times 10^{-6}$.4 km	XENON1T [10]
	Ar	$\sim 15 \text{ PE} (\sim 0.5 e^{-})$	$6780 \text{ kg} \cdot \text{d}$	$50 \mathrm{eVee}$	$> 6 \times 10^{-4}$	4 km	Darkside50 [11]

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Excesses in NR Experiments (Early 2020)



NUCLEUS surface Al₂O₃ (2017



Excesses in NR Experiments (Early 2020)



NUCLEUS surface Al₂O₃ (2017



CRESST-III CaWO₄ (2019)















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Excesses in NR Experiments (Mid 2020)



https://arxiv.org/abs/2007.15622



DAMIC @ SNOLAB Low-background Si CCD



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Excesses in NR Experiments (Mid 2020)



Plans ER/NR for Follow-up

- 1 gram-day of 0V data taken
 - Determine whether background is NR, ER, or detector-related
 - Continuous readout will allow NR limit with 9eV energy threshold
 - Coming late 2020
- More data taking at NEXUS
 - Currently operating underground, constructing lead shield
 - 3 eV resolution maintained in new facility
- Plans for larger payload, additional studies w/ high-energy gamma sources, different detector packaging



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-XENON10/100/1T rates all **similar for same threshold**



Excesses in Liquid Nobles (Early 2020)



"believed to be from electrons trapped and subsequently released by impurities" (time correlation observed)


Also Earlier this Year...

- Every [public] XENON S2-only analysis has observed a "dark rate"
- Taken together, these rates are not inconsistent!
 - This **likely** points to a source of dark rate which scales as exposure
 - ...but *could* point to DM of order 100 MeV at ~thermal cross section (just like the plasmon interpretation of the semiconductors)
 - ...particularly if you take into account Migdal contribution at lower n_e which at this mass would be additive to electron scattering signal!

→ DB, Kahn, Krnjiac [arXiv:1908.00012]



Slide Courtesy of Dan Baxter



Depth Dependence

- Si/Ge Excesses show weak to no depth dependence
 - Upcoming datasets from SuperCDMS at SNOLAB (CUTE facility) and Fermilab @ MINOS (NEXUS facility and SENSEI) will add lower variance data points
- Sapphire detector is highest excess rate
- Lowest excess in LXe and LAr, intermediate rate in Ca2O3
- Rates correlate with material more than depth



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Determining Signal Origin

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• First line of inquiry is to figure out if this is primarily an interaction with electrons or nucleons



Determining Signal Origin

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	Al_2O_3	$3.8 \mathrm{eV}$	$0.046~{\rm g}\cdot{\rm d}$	$20 \mathrm{eV}$	> 30	$\sim 1 \text{ m}$	$\nu \text{CLEUS} [8]$
Photo e^-	Xe	6.7 PE (~ $0.25 e^{-}$)	$15 \mathrm{kg} \cdot \mathrm{d}$	$12.1 \text{ eVee} (\sim 14 \text{ PE})$	$[0.5, 3] \times 10^{-4}$	1.4 km	XENON10 [5, 9]
	Xe	6.2 PE (~ $0.31 e^{-}$)	$30 \text{ kg} \cdot \text{yr}$	$\sim 70 \text{ eVee} (\sim 80 \text{ PE})$	$> 2.2 \times 10^{-5}$	1.4 km	XENON100 [5]
	Xe	< 10 PE	$60 \text{ kg} \cdot \text{yr}$	$\sim 140 \text{ eVee} (\sim 90 \text{ PE})$	$> 1.7 \times 10^{-6}$	1.4 km	XENON1T [10]
	Ar	$\sim 15 \text{ PE} (\sim 0.5 e^{-})$	6780 kg $\cdot\mathrm{d}$	50 eVee	$> 6 \times 10^{-4}$	1.4 km	Darkside50 [11]

- First line of inquiry is to figure out if this is primarily an interaction with electrons or nucleons
- The EDELWEISS data allows us to compare a total energy spectrum to a charge energy spectrum; the ratio of these values for a given energy helps identify the source of the events





 Conversion from total deposited energy (left) to charge production (right) will proceed differently depending on whether initial energy is given to electrons or nucleons

Relaxation via Phonons



- Normal processes for hot carrier relaxation are impaction ionization (liberation of additional electrons) and phonon emission
 - Electon-phonon relaxation calculated via deformation potentials; high energy electrons always emit highest energy phonons
 - Electron energy cost finite and well characterized
 - Nucleon-phonon coupling more complex, energy cost of defects much less well understood (needs to be fit phenomenologically)
 - Not defined beyond the phonon limit; relaxation of 10 eV nucleon largely un-modeled



Relaxation via Quasiparticle Creation





- Electronic excitations metastable in bulk material, energies and interactions well known
 - Electrons de-localized, strictly quantum mechanical
- Nuclear excitations myriad, energy highly dependent on momentum four-vector
 - some stable, some metastable, timescales poorly characterized
 - creation energy much greater than defect energy



Modeling Electron-Recoil Charge Yield

- For recoil energy Er, we expect a linear relationship between Ee and Er for electron-recoil processes
 - Poorly measured with photons below 100 eV (only one reference)
 - No measurements of charge yield for energy between ~5 eV and ~100 keV for electrons or protons
- Need this conversion to be able to compare Ee and Edet results.
 - If we believe it's linear across all energy scales, we can make some general observations
- Indirect measurements come from Electron Energy Loss Spectroscopy (EELS)



Ramanathan and Kurinsky, https://arxiv.org/abs/2004.10709

$$E_e = E_{det} \left[y(E_{det}) + \frac{\epsilon_{eh}}{e \cdot V_{det}} \right]$$



Understanding Low-Energy NR Yield

https://arxiv.org/pdf/2001.06503.pdf



NR charge yield completely un-measured in Si below ~500 eV, very few measurements below 1 keV in Ge

- LHe/LAr have a similar problem, but preliminary results suggest highly non-linear response in the low-energy region

- Consensus growing in the field that ~300 eV NR events will not generate charge in Si/Ge, similar effects for other solid-state detector technologies
 - Phenomenological model fits ~150 eV loss to nuclear lattice effects
- Displacement thresholds in Si/Ge are ~20-40 eV; at this scale, the picture off a recoiling nucleus is incorrect. Where
 between 20 eV and 1 keV does this really start to break down?
 - Plasmon has an energy of ~17 eV in both materials (24 eV in Al2O3)



Electron Recoil Interpretation



ER only prediction can't fit under black curve: BAD FIT



Elastic Nuclear Recoil Interpretation



NR only prediction can't fit under black curve: BAD FIT

‡ Fermilab

Elastic Nuclear Recoil Interpretation





Model can fit under the black curve: 0V spectrum is consistent with HV spectrum only for highly inelastic yield curves



Consider Semiconductor Plasmons

Long wavelength charge oscillation between electrons/ions >> lattice spacing

phonons (momentum)



Plasmon excitation energy

$$E_p \simeq \sqrt{\frac{4\pi\alpha n_e}{m_e}}$$

Low-P standing wave decays to e/h pairs or phonons Breaks usual charge heat yield relationship





Electron Energy-Loss Spectroscopy (EELS)



MK Kundmann PhD Thesis 1988

😤 Fermilab

- SM Backgrounds?
 - Neutrinos
 - Photons
 - Protons/Electrons
 - Muons
 - Neutrons
- Experimental Effects?
 - Crystal Cracking
 - Non-poissonian leakage
 - Low-frequency noise
 - Earthquakes
 - Your Model Here



• SM Backgrounds?

- Noutrinoo

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Figure from Gordan Krnjaic



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S(w) as a function of energy transfered by the incident photon



The different plots represent different approximations of S(q,w) (different local field corrections G(q,w) We see that near the plasmon frequency, S(w) goes as high as 25; which means the Compton differential cross section on silicon valence electrons is around 25 times the differential cross section on free electrons.

At these low q, S(w) is dominated by plasmons, and we should therefore see a peak above the compton scattering background caused by plasmon production.

Emile Michaud Photon Production of Plasmon Talk

Small Enhancement to Compton Rate



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SENSEI Observes some reduction in lowenergy charge excess with additional shielding, possibly indicative of gamma-induced secondary radiation (can't explain CRESST)



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Protons/Electrons: mean free path too small, single scattering not possible for thick detectors (also true for < 1 keV photons)



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 - Noutrinoo
 - Photons -

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Direct Production by Muons not possible...has to be non-linear, metastable coupling. More data can fully rule out depth dependence.



- SM Backgrounds?
 - Neutrinos - Photons -Protons/Electrons - Muons
 - Neutrons ?
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- New Physics?

Possible in principle Neutron could scatter nucleus, excite secondary plasmon Possible calibration strategy

Baxter, Kahn, Kurinsky, GK [in preparation]

Hard to explain all excesses this way

Different Depths Different Shielding Different Exposures Different Composition

Why is the neutron flux independent of these factors?

Slide from Gordan Krnjaic



• SM Backgrounds?



-- Photons -

- Muorts
- Neutrons ?
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 - Non-poissonian leakage
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Technology and detector dependent, Should not

produce charge, could produce heat only signals



• SM Backgrounds?



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No known mechanism for correlated leakage Shouldn't be the same for CCDs (100K) and Calorimeters (10 mK)



Possible Sources of Excesses



• SM Backgrounds?



• New Physics?

‡ Fermilab

- SM Backgrounds?
 - Photons

Protons/Electrons

- -- Muorts
- Neutrons ?
- Experimental Effects?
 - Crystal Cracking ?
 Non poissonian loakage
 Low frequency noise

Earthquakaa

- Your Model Here
- New Physics?

Remaining options are highly non-linear, metastable couplings, odd types of photon or neutron flux that do not respect shielding, or some new physics.

More background modeling encouraged...help us understand this!

At what point do we start to decide that this really could be dark matter?



Direct Plasmon Production DM Model

- DM couples to electrons.
- Direct plasmon production occurs as it does for electrons, but with a much longer mean free path
 - Calibrated by EELS...plasmon definitely produced
- DM has to be faster than the escape velocity
 - It should be an accelerated subcomponent, which can be produced in supernovae or in the sun



- DM couples to nucleons.
- Plasmons and phonons (and a little bit of charge) produced as nucleus relaxes
 - Defect energy cost is ~10-20 eV in Si/Ge, higher in sapphire







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Parametrize our ignorance



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 $\left[\mathrm{cm}^{2}\right]$

 σ_p

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 - Preferred region at 30-1000 MeV
 - Dark photon model viable!



First-Principles Calculations: Plasmon Bremsstrahlung

- Follow-up study calculates plasmon production due to NR with a single phonon in the final state
 - Kinematics are distinct from those described previously, but set a lower bound on the total rate
 - Bound is already comparable to migdal, and suggests that total rate is much larger when accounting for multi-phonon scattering
- Sits at the opposite regime compared to the NR charge yield calculations, coming from NR-phonon scattering





Moving Forward

- Push forward calibration efforts to better under NR detector response and role of collective effects below 1 keV
- Building collaboration to push forward understanding of 10 eV to 1 keV ER/ NR response in semiconductors

Snowmass2021 - Letter of Interest

Sub GeV DM-Nucleon Scattering via Collective Excitations: The Inelastic Regime.

Thematic Areas:

(CF1) Cosmic Frontier: Dark Matter: Particle Like
 (TF9) Theory Frontier: Astro-particle physics and cosmology

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Dielectric Function Formalism

 In the low-energy regime, we can express electromagnetic interactions in terms of the loss function:

$$\frac{\mathrm{d}^2\sigma}{\mathrm{d}\Omega_2\mathrm{d}\hbar\omega_2} = r_0^2(\mathbf{e}_1\cdot\mathbf{e}_2)^2\left(\frac{\omega_2}{\omega_1}\right)S(\mathbf{q},\omega), \quad r_0 = \frac{e^2}{mc^2}$$

• This same language can be used to describe DM interactions, because the structure factor is only determined by interactions within the target material:

$$\Gamma(\mathbf{v}_{\chi}) = \int \frac{\mathrm{d}^{3}\mathbf{q}}{(2\pi)^{3}} |V(\mathbf{q})|^{2} \left[2\frac{q^{2}}{e^{2}} \operatorname{Im}\left(-\frac{1}{\epsilon(\mathbf{q},\omega_{\mathbf{q}})}\right)\right]$$

- The loss function is well-characterized in the literature, and toy models exist for different types of materials - doesn't require detailed DFT calculations
- Upcoming paper explores a handful of new materials with data and toy models, reducing turnaround on material exploration from years to months
 - Also allows us to determine generic features of a material useful for DM detection in different models

Berggren, Hochberg, Kahn, NK, Lehman, Yu, ArXiv:2101.08263



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Conclusions

- Many experiments have begun to see low-energy excesses that are consistent with DM when inelasticity of the medium is accounted for.
- There is not a consistent story of a background or DM signal that can conclusively explain all excesses
 - Some excesses are likely un-modeled backgrounds related to secondary and tertiary production of low-energy photons and charged particles
 - Other excesses, which do not scale with shielding or environment, are harder to explain
 - Rates are strongly dependent on the medium used to detect events, and seem to correlate with the degree of regularity of the medium
- We are probing a regime in which DM is viable, and material responses are largely uncalibrated
- There is a ton of growth potential and discovery potential in these mass and energy regimes!